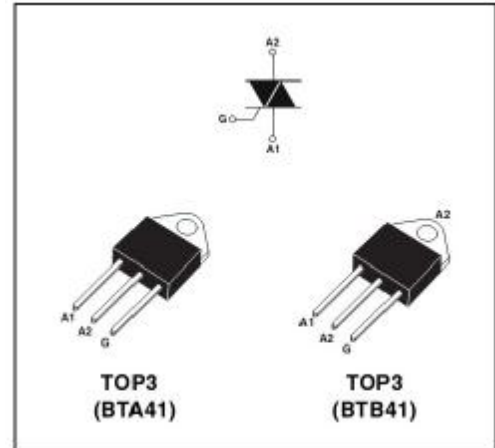


: YUi fYg.

- NPNPN Bi-direction Triac
- Back multilayer metal electrode
- High temperature reliability
- Glass Passivated junction chipsets

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• Limiting Values

Symbol	Absolute maximum ratings parameters		Value	Unit
$I_{T(RMS)}$	RMS on-state current	BTA BTB	Tc=80°C Tc=90°C	40 A
I_{TSM}	Non repetitive surge peak on-state current		F=50HZ t=20ms	410 A
i^2t	I ² t value for fusing		tp=10ms	880 A ² S
di/dt	Critical rate of rise of on-state current		Tj=125°C	50 A/us
VDRM/VRRM	Non repetitive surge peak off-state voltage		Tj=25°C	800 V
IGM	Peak gate current	tp=20us	Tj=125°C	8 A
PG(AV)	Average gate power dissipation		Tj=125°C	1 W
Tstg	Storage junction temperature range			-40to+150 °C
Tj	Operating junction temperature range			-40to+125 °C

• **Electrical Characteristics(4 quadrant) (T_j=25°C, unless otherwise specified)**

Symbol	Test Condition	Quadrant		Value	Unit	
I _{GT}	V _D =12V R _L =100Ω	I II III IV	MAX	I II IV	mA	
V _{GT}				5		IV
V _{GD}	T _j =125°C		MIN	1.5		V
I _H	I _T =0.5A		MAX	0.2		V
I _L	I _G =1.2I _{GT}	I II IV	MAX	80		mA
		IV		70		
dv/dt	V _D =2/3V _{DRM} T _j =125°C		MIN	160		V/us
(dv/dt) _c	T _j =125°C		MIN	800		
				10		V/us

• **Static Characteristics**

Symbol	Test Conditions			Value	Unit
V _{TM}	I _{TM} = 82A	T _j =25°C	MAX	1.55	V
V _{T0}	Threshold voltage	T _j =125°C	MAX	0.86	V
R _d	Dynamic resistance	T _j =125°C	MAX	6.4	mΩ
I _{DRM} I _{RDM}	V _{DRM} = V _{DRM}	T _j =25°C	MAX	10	uA
		T _j =125°C		2	mA
R _{th(j-c)}	Junction to case (AC)	BTA		0.9	°C/W
		BTB		0.6	

